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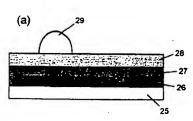
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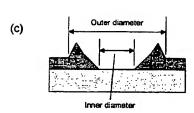
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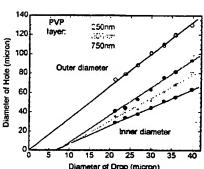
(54) Title: FORMING INTERCONNECTS



(57) Abstract: A method for forming an electronic device, comprising: forming a first conductive or semiconductive layer; forming a sequence of at least one insulating layer and at least one semiconducting layer over the first conductive or semiconductive layer; locally depositing solvents at a localised region of the insulating layer so as to dissolve the sequence of insulating and semiconducting layers in the region to leave a void extending through the sequence of layers; and depositing conductive or semiconductive material in the void.







WO 01/47044 AS



patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG).

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CLASSIFICATION OF SUBJECT MATTER PC 7 H01L51/40 H01L21/311	
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ccording to International Patent Classification (IPC) or to both national classification and IPC	
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INSPEC, EPO-Internal	
DOCUMENTS CONSIDERED TO BE RELEVANT	Relevant to claim No.
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X Further documents are listed in the continuation of box C. X Patent family members are listed in annual	9x.
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19 February 2001 .1 8. 05. 01	
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NL - 2280 HV Flüswijk Tel. (+31-70) 340-2040, Tx. 31 651 epo rd. Fax: (+31-70) 340-3018 Königstein, C	

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C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT						
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A	EP 0 930 641 A (SEIKO EPSON CORP) 21 July 1999 (1999-07-21) the whole document	1				
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ational application No. PCT/GB 00/04940

Box I Observations where certain claims were found unsearchable (Continuation of item 1 of first sheet)
This International Search Report has not been established in respect of certain claims under Article 17(2)(a) for the following reasons:
1. Claims Nos.: because they relate to subject matter not required to be searched by this Authority, namely:
 Claims Nos.: because they relate to parts of the International Application that do not comply with the prescribed requirements to such an extent that no meaningful International Search can be carried out, specifically:
3. Claims Nos.: because they are dependent claims and are not drafted in accordance with the second and third sentences of Rule 6.4(a).
Box II Observations where unity of invention is lacking (Continuation of item 2 of first sheet)
This International Searching Authority found multiple inventions in this international application, as follows:
see additional sheet
As all required additional search fees were timely paid by the applicant, this International Search Report covers all searchable claims.
2. As all searchable claims could be searched without effort justifying an additional fee, this Authority did not invite payment of any additional fee.
3. As only some of the required additional search fees were timety paid by the applicant, this International Search Report covers only those claims for which fees were paid, specifically claims Nos.:
4. No required additional search fees were timely paid by the applicant. Consequently, this International Search Report is restricted to the invention first mentioned in the claims; it is covered by claims Nos.:
1-38,44-49
Remark on Protest The additional search fees were accompanied by the applicant's protest.
No protest accompanied the payment of additional search fees.

FURTHER INFORMATION CONTINUED FROM PCT/ISA/ 210

This International Searching Authority found multiple (groups of) inventions in this international application, as follows:

1. Claims: 1-38,44-49

Patterning of organic insulating layers by selective etching

The prior Art describes a field effect transistor substantially consisting of organic materials.

The new features mentioned in claims 1-38 are contact holes, made in organic dielectric layers by wet etching using an ink-jet printing system to locally suply the etch liquid.

From this we can formulate an objective problem of making contact holes in organic dielectric layers by wet etching using an ink-jet printing system to locally suply the etch liquid.

The special technical features, as defined in Rule 13(2) PCT, are contact holes, made in organic dielectric layers by wet etching using an ink-jet printing system to locally suply the etch liquid.

2. Claims: 39-43

Selective doping of organic insulating layers

The prior Art describes a field effect transistor substantially consisting of organic materials.

The new features mentioned in claims 1-38 are conductive (interconnection) patterns made by selective doping organic insulating layers to make them conductive. The dopants are applied using an ink-jet printing system.

From this we can formulate an objective problem of making conductive patterns made by selective doping organic insulating layers to make them conductive, applying the dopants are using an ink-jet printing system.

The special technical features, as defined in Rule 13(2) PCT, are conductive (interconnection) patterns made by selective doping organic insulating layers to make them conductive. The dopants are applied using an ink-jet printing system.

atornation on patent family members

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